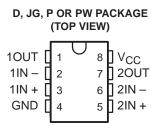
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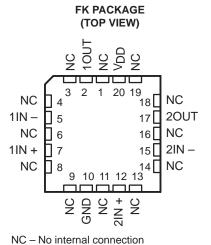
- **Trimmed Offset Voltage:** TLC27M7 . . . 500 μV Max at 25°C, $V_{DD} = 5 V$
- Input Offset Voltage Drift . . . Typically 0.1 μV/Month, Including the First 30 Days
- Wide Range of Supply Voltages Over **Specified Temperature Ranges:**

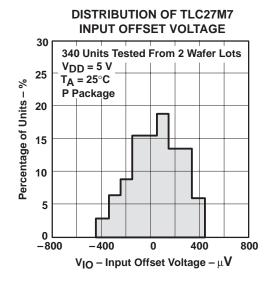
 0° C to 70° C . . . 3 V to 16 V -40°C to 85°C . . . 4 V to 16 V -55°C to 125°C . . . 4 V to 16 V

- **Single-Supply Operation**
- **Common-Mode Input Voltage Range Extends Below the Negative Rail (C-Suffix, I-Suffix Types**)

- Low Noise . . . Typically 32 nV/√Hz at f = 1 kHz
- Low Power . . . Typically 2.1 mW at 25°C, $V_{DD} = 5 V$
- **Output Voltage Range Includes Negative**
- High Input impedance . . . $10^{12} \Omega$ Typ
- **ESD-Protection Circuitry**
- **Small-Outline Package Option Also** Available in Tape and Reel
- **Designed-In Latch-Up Immunity**







AVAILABLE OPTIONS

	V _{IO} max			PACKAGE		
TA	AT 25°C	SMALL OUTLINE (D)	CHIP CARRIER (FK)	CERAMIC DIP (JG)	PLASTIC DIP (P)	TSSOP (PW)
	500 μV	TLC27M7CD	_	_	TLC27M7CP	_
0°C to 70°C	2 mV	TLC27M2BCD	_	_	TLC27M2BCP	_
0 0 10 70 0	5 mV	TLC27M2ACD	_	_	TLC27M2ACP	_
	10 mV	TLC27M2CD	_	_	TLC27M2CP	TLC27M2CPW
	500 μV	TLC27M7ID	_	_	TLC27M7IP	_
-40°C to 85°C	2 mV	TLC27M2BID	_	_	TLC27M2BIP	_
-40 C to 65 C	5 mV	TLC27M2AID	_	_	TLC27M2AIP	_
	10 mV	TLC27M2ID	_	_	TLC27M2IP	TLC27M2IPW
-55°C to 125°C	500 μV	TLC27M7MD	TLC27M7MFK	TLC27M7MJG	TLC27M7MP	_
-33 C to 125 C	10 mV	TLC27M2MD	TLC27M2MFK	TLC27M2MJG	TLC27M2MP	_

The D and PW package is available taped and reeled. Add R suffix to the device type (e.g., TLC27M7CDR).

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description

The TLC27M2 and TLC27M7 dual operational amplifiers combine a wide range of input offset voltage grades with low offset voltage drift, high input impedance, low noise, and speeds approaching that of general-purpose bipolar devices. These devices use Texas Instruments silicon-gate LinCMOS technology, which provides offset voltage stability far exceeding the stability available with conventional metal-gate processes.

The extremely high input impedance, low bias currents, and high slew rates make these cost-effective devices ideal for applications which have previously been reserved for general-purpose bipolar products, but with only a fraction of the power consumption. Four offset voltage grades are available (C-suffix and I-suffix types), ranging from the low-cost TLC27M2 (10 mV) to the high-precision TLC27M7 (500 μ V). These advantages, in combination with good common-mode rejection and supply voltage rejection, make these devices a good choice for new state-of-the-art designs as well as for upgrading existing designs.

In general, many features associated with bipolar technology are available on LinCMOS™ operational amplifiers, without the power penalties of bipolar technology. General applications such as transducer interfacing, analog calculations, amplifier blocks, active filters, and signal buffering are easily designed with the TLC27M2 and TLC27M7. The devices also exhibit low voltage single-supply operation, making them ideally suited for remote and inaccessible battery-powered applications. The common-mode input voltage range includes the negative rail.

A wide range of packaging options is available, including small-outline and chip-carrier versions for high-density system applications.

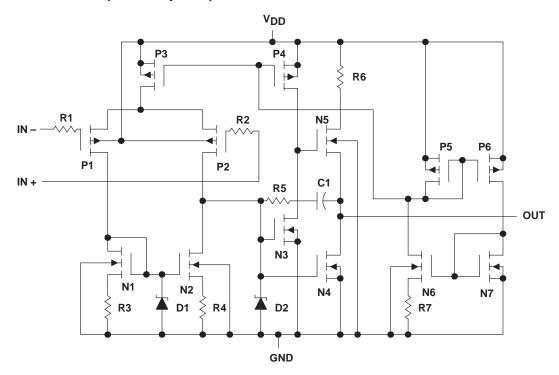
The device inputs and outputs are designed to withstand -100-mA surge currents without sustaining latch-up.

The TLC27M2 and TLC27M7 incorporate internal ESD-protection circuits that prevent functional failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015.2; however, care should be exercised in handling these devices as exposure to ESD may result in the degradation of the device parametric performance.

The C-suffix devices are characterized for operation from 0° C to 70° C. The I-suffix devices are characterized for operation from -40° C to 85° C. The M-suffix devices are characterized for operation over the full military temperature range of -55° C to 125° C.



equivalent schematic (each amplifier)



TLC27M2, TLC27M2A, TLC27M2B, TLC27M7 Lincmos™ Precision dual operational amplifiers

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, V _{DD} (see Note 1)	
Differential input voltage, V _{ID} (see Note 2)	±V _{DD}
Input voltage range, V _I (any input)	– 0.3 V to V _{DD}
Input current, I _I	±5 mA
Output current, IO (each output)	±30 mA
Total current into V _{DD}	45 mA
Total current out of GND	45 mA
Duration of short-circuit current at (or below) 25°C (see Note 3)	Unlimited
Continuous total dissipation	. See Dissipation Rating Table
Operating free-air temperature, T _A : C suffix	0°C to 70°C
I suffix	–40°C to 85°C
M suffix	–55°C to 125°C
Storage temperature range	–65°C to 150°C
Case temperature for 60 seconds: FK package	260°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: D or P packa	age 260°C
Lead temperature 1,6 mm (1/16 inch) from case for 60 seconds: JG package	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential voltages, are with respect to network ground.
 - 2. Differential voltages are at IN+ with respect to IN-.
 - 3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded (see application section).

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{A}} \le 25^{\circ}\mbox{C}$ POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING	T _A = 125°C POWER RATING
D	725 mW	5.8 mW/°C	464 mW	377 mW	
FK	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
JG	1050 mW	8.4 mW/°C	672 mW	546 mW	210 mW
Р	1000 mW	8.0 mW/°C	640 mW	520 mW	

recommended operating conditions

		C SU	FFIX	I SUF	FIX	M SU	FFIX	UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	UNIT
Supply voltage, V _{DD}		3	16	4	16	4	16	V
Common mode input voltage V	V _{DD} = 5 V	-0.2	3.5	-0.2	3.5	0	3.5	V
Common-mode input voltage, V _{IC}	V _{DD} = 10 V	-0.2	8.5	-0.2	8.5	0	8.5	V
Operating free-air temperature, TA		0	70	-40	85	-55	125	°C



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electrical characteristics at specified free-air temperature, V_{DD} = 5 V (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS	T _A †	TL TL	.C27M2 .C27M2 .C27M2 .C27M7	AC BC	UNIT
		_				MIN	TYP	MAX	
		TLC27M2C	$V_0 = 1.4 V$	$V_{IC} = 0$,	25°C		1.1	10	
		TEOZTWZO	$R_S = 50 \Omega$,	$R_{\parallel} = 100 \text{ k}\Omega$	Full range			12	mV
		TLC27M2AC	V _O = 1.4 V,	$V_{IC} = 0$,	25°C		0.9	5	IIIV
VIO	Input offset voltage	TEGZTWIZAG	$R_S = 50 \Omega$,	$R_I = 100 \text{ k}\Omega$	Full range			6.5	
1 10	input onset voltage	TLC27M2BC	$V_0 = 1.4 V$	$V_{IC} = 0$,	25°C		220	2000	
		TEGZTWIZBC	$R_S = 50 \Omega$,	$R_{\parallel} = 100 \text{ k}\Omega$	Full range			3000	μV
		TLC27M7C	V _O = 1.4 V,	$V_{IC} = 0$,	25°C		185	500	μν
		TEGZTWITE	$R_S = 50 \Omega$,	$R_I = 100 \text{ k}\Omega$	Full range			1500	
αVIO	Average temperature coe offset voltage	efficient of input			25°C to 70°C		1.7		μV/°C
	land offert compat (co.	Mata 4)	V 05V	V 0.5.V	25°C		0.1		^
lio	Input offset current (see	Note 4)	$V_0 = 2.5 V$,	$V_{IC} = 2.5 V$	70°C		7	300	pΑ
	Lament his a summer to a a Ni	-1- 1)	V 05V	V 0.5.V	25°C		0.6		A
IВ	Input bias current (see N	ote 4)	$V_0 = 2.5 V$,	$V_{IC} = 2.5 V$	70°C		40	600	pΑ
						-0.2	-0.3		
					25°C	to	to		V
VICR	Common-mode input vol (see Note 5)	tage range				4	4.2		
	(See Note 3)				Full range	-0.2 to			V
					1	3.5			
					25°C	3.2	3.9		
Vон	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 100 \text{ k}\Omega$	0°C	3	3.9		V
					70°C	3	4		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	0°C		0	50	mV
					70°C		0	50	
					25°C	25	170		
AVD	Large-signal differential vamplification	roltage	$V_0 = 0.25 \text{ V to 2 V},$	$R_L = 100 \text{ k}\Omega$	0°C	15	200		V/mV
	amplification				70°C	15	140		
					25°C	65	91		
CMRR	Common-mode rejection	ratio	V _{IC} = V _{ICR} min		0°C	60	91		dB
					70°C	60	92		
					25°C	70	93		
kSVR	Supply-voltage rejection (ΔV _{DD} /ΔV _{IO})	ratio	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	0°C	60	92		dB
	(AADD)(AAIO)				70°C	60	94		
			.,		25°C		210	560	
I _{DD}	Supply current (two amp	ifiers)	V _O = 2.5 V, No load	$V_{IC} = 2.5 V$,	0°C		250	640	μΑ
					70°C		170	440	

[†] Full range is 0°C to 70°C.



^{5.} This range also applies to each input individually.

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electrical characteristics at specified free-air temperature, V_{DD} = 10 V (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS	τ _A †	TL TL TL	.C27M2 .C27M2 .C27M2 .C27M7	AC BC C	UNIT
		 				MIN	TYP	MAX	
		TLC27M2C	V _O = 1.4 V,	$V_{IC} = 0$,	25°C		1.1	10	
			$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			12	mV
		TLC27M2AC	V _O = 1.4 V,	V _{IC} = 0,	25°C		0.9	5	
VIO	Input offset voltage		$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			6.5	
		TLC27M2BC	V _O = 1.4 V,	V _{IC} = 0,	25°C		224	2000	
			$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			3000	μV
		TLC27M7C	$V_0 = 1.4 \text{ V},$	$V_{IC} = 0$,	25°C		190	800	ļ .
			$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			1900	
αVIO	Average temperature coe offset voltage	efficient of input			25°C to 70°C		2.1		μV/°C
lio.	Input offset current (see I	Note 4)	V _O = 5 V,	V _{IC} = 5 V	25°C		0.1		pА
IO	input onset current (see i	NOTE 4)	VO = 3 V,	AIC = 2 A	70°C		7	300	PΑ
lun.	Input bigg ourrent (see N	oto 4)	V _O = 5 V,	\/.o - F \/	25°C		0.7		π Λ
ΙΒ	Input bias current (see N	ote 4)	VO = 2V	$V_{IC} = 5 V$	70°C		50	600	pΑ
	Common-mode input vol	tage range			25°C	-0.2 to 9	-0.3 to 9.2		V
VICR	(see Note 5)				Full range	-0.2 to 8.5			V
					25°C	8	8.7		
Vон	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 100 \text{ k}\Omega$	0°C	7.8	8.7		V
					70°C	7.8	8.7		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	0°C		0	50	mV
					70°C		0	50	
					25°C	25	275		
AVD	Large-signal differential v amplification	roltage	$V_0 = 1 V \text{ to } 6 V,$	$R_L = 100 \text{ k}\Omega$	0°C	15	320		V/mV
1	апрішовіон				70°C	15	230		
					25°C	65	94		
CMRR	Common-mode rejection	ratio	V _{IC} = V _{ICR} min		0°C	60	94		dB
1					70°C	60	94		
					25°C	70	93		
ksvr	Supply-voltage rejection (ΔV _{DD} /ΔV _{IO})	ratio	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	0°C	60	92		dB
	(AADD/AAIQ)				70°C	60	94		
			.,,		25°C		285	600	
I_{DD}	Supply current (two ampl	ifiers)	V _O = 5 V, No load	$V_{IC} = 5 V$	0°C		345	800	μΑ
1					70°C		220	560	

[†] Full range is 0°C to 70°C.



^{5.} This range also applies to each input individually.

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electrical characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$ (unless otherwise noted)

$V_{IO} = \frac{1}{N_{IO}} = \frac{1}{N_{IO$		PARAMETER		TEST CON	DITIONS	TAT	TL TL TL	.C27M2I .C27M2/ .C27M2I .C27M7I	AI BI	UNIT
Vio Input offset voltage TLC27M2I RS = 50 Ω RL = 100 kΩ Full range 13 m/ RS = 50 Ω RL = 100 kΩ Full range 7 m/ RS = 50 Ω RL = 100 kΩ Full range 7 m/ RS = 50 Ω RL = 100 kΩ Full range 7 m/ RS = 50 Ω RL = 100 kΩ Full range 7 m/ RS = 50 Ω RL = 100 kΩ Full range 3500 m/ RS = 50 Ω RL = 100 kΩ Full range 3500 m/ RS = 50 Ω RL = 100 kΩ Full range 3500 m/ RS = 50 Ω RL = 100 kΩ Full range 3500 m/ RS = 50 Ω RL = 100 kΩ Full range 3500 m/ RS = 50 Ω RL = 100 kΩ Full range 3500 m/ RS = 50 Ω RL = 100 kΩ Full range 3500 m/ RS = 50 Ω RL = 100 kΩ Full range 3500 m/ RS = 50 Ω RL = 100 kΩ Full range 3500 m/ RS = 50 Ω RL = 100 kΩ Full range 3500 m/ RS = 50 Ω RL = 100 kΩ Full range 3500 m/ RS = 50 Ω RL = 100 kΩ Full range 3500 m/ RS = 50 Ω RL = 100 kΩ Full range 3500 m/ RS = 50 Ω RL = 100 kΩ Full range 3500 m/ RS = 50 Ω RL = 100 kΩ Full range 3500 m/ RS = 50 Ω RL = 100 kΩ Full range 3500 m/ RS = 50 Ω RL = 100 kΩ Full range 3500 m/ RS = 50 Ω Full range 3					,		MIN	TYP	MAX	
Vical Input offset voltage TLC27M2AI Vical			TLC27M2I					1.1		
$V_{IO} \text{Input offset voltage} \begin{array}{ c c c c c c }\hline TLC27MZAI & V_{O} = 1.4 \ V, \\ R_S = 50 \ \Omega, & R_L = 100 \ \text{k}\Omega \\\hline TLC27MZBI & V_O = 1.4 \ V, \\ R_S = 50 \ \Omega, & R_L = 100 \ \text{k}\Omega \\\hline TLC27MZII & V_O = 1.4 \ V, \\ R_S = 50 \ \Omega, & R_L = 100 \ \text{k}\Omega \\\hline TLC27MZII & V_O = 1.4 \ V, \\ R_S = 50 \ \Omega, & R_L = 100 \ \text{k}\Omega \\\hline TLC27MZII & V_O = 1.4 \ V, \\ R_S = 50 \ \Omega, & R_L = 100 \ \text{k}\Omega \\\hline Pull range & 3500 \\ Full range & 2000 \\\hline Full$				$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	+				mV
$V_{IC} = \begin{array}{ c c c c c c c c } & Input offset voltage & R_S = 50 \Omega, & R_I = 100 k\Omega & Full range & 7 \\ \hline TLC27M2BI & R_S = 50 \Omega, & R_I = 100 k\Omega & Full range & 3500 \\ \hline TLC27M7I & V_O = 1.4 V, & V_{IC} = 0, & 25^{\circ}C & 185 & 500 \\ \hline TLC27M7I & V_O = 1.4 V, & V_{IC} = 0, & 25^{\circ}C & 185 & 500 \\ \hline R_I = 100 k\Omega & Full range & 2000 \\ \hline R_I = 100 k\Omega & Full range & 2000 \\ \hline R_I = 100 k\Omega & Full range & 2000 \\ \hline R_I = 100 k\Omega & Full range & 2000 \\ \hline R_I = 100 k\Omega & Full range & 2000 \\ \hline R_I = 100 k\Omega & R_I = 100 k\Omega & Full range & 2000 \\ \hline R_I = 100 k\Omega & R_I = 100 k\Omega & R_I = 100 k\Omega \\ \hline R_I = 100 k\Omega & R_I = 100 k$			TLC27M2AI					0.9		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Vio	Input offset voltage		$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	+			7	
RS = 50 Ω RL = 100 kΩ Full range 3500 pt TLC27M7I V _O = 1.4 V, RS = 50 Ω RL = 100 kΩ Full range 2000 CVIO Average temperature coefficient of input offset voltage 25°C to 85°C 1.7 pt Ito Input offset current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V 85°C 24 1000 pA Itig Input bias current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V 85°C 24 1000 pA Itig Input bias current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V 85°C 200 2000 pA Itig Input bias current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V 85°C 200 2000 pA Itig Input bias current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V 85°C 200 2000 pA Itig Input bias current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V 25°C 0.6 pA VICR Common-mode input voltage range (see Note 5) V _{ID} = 100 mV, R _L = 100 kΩ 25°C 3.2 3.9 V _{ID} = 100 mV, R _L = 100 kΩ 25°C 3.2 3.9 V _{ID} = 100 mV, R _L = 100 kΩ 25°C 0.50 mV VOL Low-level output voltage V _{ID} = -100 mV, I _{OL} = 0 25°C 0.50 50 mV Large-signal differential voltage amplification V _{ID} = 0.25 V to 2 V, R _L = 100 kΩ 25°C 25 170 V/m Extraction V _{ID} = 0.25 V to 2 V, R _L = 100 kΩ 25°C 65 91 CMR 25°C 65 91 CMR 25°C 60 90 CMR	"	,	TLC27M2BI					220	2000	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$				$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$					иV
Average temperature coefficient of input offset voltage 25°C to 25°C to 25°C to 25°C to 385°C 24 1000 25°C to 25°C 25°			TLC27M7I			25°C		185	500	
In Input offset current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V 25°C 0.1 85°C 24 1000 PA				$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$				2000	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	αVIO		ficient of input					1.7		μV/°C
It It It It It It It It	1	Input offset surrent (see N	loto 4)	Va - 2 5 V	V 2.5.V	25°C		0.1		n /
No No No No No No No No	110	input onset current (see N	lote 4)	VO = 2.5 V,	AIC = 5.9 A	85°C		24	1000	PΑ
VICR Common-mode input voltage range (see Note 5) VID = 100 mV, RL = 100 kΩ 25°C 200 2000 VID = 100 mV, RL = 100 kΩ 25°C 3.2 3.9 VID = 100 mV, RL = 100 kΩ 25°C 3.2 3.9 VID = 100 mV, IDL = 0 25°C 0 50 MV 25°C 25 170 VID = 100 mV, RL = 100 kΩ 25°C 25 170 VID = 100 mV, RL = 100 kΩ 25°C 25 170 VID = 100 mV, RL = 100 kΩ 25°C 25 170 VID = 100 mV, RL = 100 kΩ 25°C 25 170 VID = 100 mV, RL = 100 kΩ 25°C 25 170 VID = 100 mV, RL = 100 kΩ 25°C 25 170 VID = 100 mV, RL = 100 kΩ 25°C 25 170 VID = 100 mV, RL = 100 kΩ 25°C 25 170 VID = 100 mV, RL = 100 kΩ 25°C 25 170 VID = 100 mV, RL = 100 kΩ 25°C 25 170 VID = 100 mV, RL = 100 kΩ 25°C 25 170 VID = 100 mV, RL = 100 kΩ 25°C 25 170 VID = 100 mV, RL = 100 kΩ 25°C 200 mV, RL = 100 kΩ 200 mV, R	1	lanut bina aumant (ana Na	4- 4)	V- 05V	V 0.5.V	25°C		0.6		^
$V_{ICR} = \begin{array}{c} Common-mode input voltage range \\ (see Note 5) \end{array} \\ V_{ICR} = \begin{array}{c} Common-mode input voltage range \\ (see Note 5) \end{array} \\ V_{ID} = \begin{array}{c} 100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = 100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = 100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ \\ V_{ID} = -100 \text{ mV}, & R_L = 100 \text{ k}\Omega \\ \hline \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ $	l'IB	input bias current (see No	te 4)	VO = 2.5 V,	AIC = 5.2 A	85°C		200	2000	рA
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$							-0.2	-0.3		
VicR (see Note 5) Vic						25°C				V
$V_{OH} \text{High-level output voltage} V_{ID} = 100 \text{mV}, R_L = 100 \text{k}\Omega \qquad \frac{25^\circ\text{C}}{85^\circ\text{C}} 3.2 3.9 \\ V_{OL} \text{Low-level output voltage} \qquad V_{ID} = -100 \text{mV}, I_{OL} = 0 \qquad \frac{25^\circ\text{C}}{85^\circ\text{C}} 0 50 \\ \hline V_{OL} \text{Low-level output voltage} \qquad V_{ID} = -100 \text{mV}, I_{OL} = 0 \qquad \frac{25^\circ\text{C}}{85^\circ\text{C}} 0 50 \\ \hline \text{Mod} \text{Mod} $	VICR		age range					4.2		
$V_{OH} \text{High-level output voltage} \qquad V_{ID} = 100 \text{mV}, R_L = 100 \text{k}\Omega \qquad \frac{25^{\circ}\text{C}}{85^{\circ}\text{C}} \qquad 3.2 3.9}{85^{\circ}\text{C}} \qquad 3 4 \qquad V_{ID} = 100 \text{mV}, R_L = 100 \text{k}\Omega \qquad \frac{25^{\circ}\text{C}}{85^{\circ}\text{C}} \qquad 3 4 \qquad V_{ID} = 100 \text{mV}, I_{OL} = 0 \qquad \frac{25^{\circ}\text{C}}{85^{\circ}\text{C}} \qquad 0 50}{85^{\circ}\text{C}} \qquad 0 50} \text{mV}$ $V_{OL} \text{Low-level output voltage} \qquad V_{ID} = -100 \text{mV}, I_{OL} = 0 \qquad \frac{25^{\circ}\text{C}}{85^{\circ}\text{C}} \qquad 0 50}{85^{\circ}\text{C}} \qquad 0 50} \text{mV}$ $A_{VD} \text{Large-signal differential voltage} V_{O} = 0.25 \text{V to 2 V}, R_L = 100 \text{k}\Omega \qquad \frac{25^{\circ}\text{C}}{85^{\circ}\text{C}} \qquad 15 270}{85^{\circ}\text{C}} \qquad 0.50} \text{V/m}$ $CMRR \text{Common-mode rejection ratio} \qquad V_{IC} = V_{ICRmin} \qquad \frac{25^{\circ}\text{C}}{85^{\circ}\text{C}} \qquad 60 90}{85^{\circ}\text{C}} \qquad 60 90} \text{dE}$ $k_{SVR} \text{Supply-voltage rejection ratio} \qquad V_{DD} = 5 \text{V to 10 V}, V_{O} = 1.4 \text{V} \qquad \frac{25^{\circ}\text{C}}{85^{\circ}\text{C}} \qquad 60 91}{85^{\circ}\text{C}} \qquad 60 91} \text{dE}$ $V_{DD} = 5 \text{V to 10 V}, V_{O} = 1.4 \text{V} \qquad \frac{25^{\circ}\text{C}}{85^{\circ}\text{C}} \qquad 60 91}{85^{\circ}\text{C}} \qquad 60 91} \text{dE}$		(See Note 3)				Full range				V
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$						l an range				·
$V_{OL} \text{Low-level output voltage} \qquad V_{ID} = -100 \text{mV}, I_{OL} = 0 \qquad \begin{array}{c} 85^{\circ}\text{C} & 3 & 4 \\ \hline 25^{\circ}\text{C} & 0 & 50 \\ \hline 85^{\circ}\text{C} & 0 & 50 \\ \hline 85^{\circ}\text{C} & 0 & 50 \\ \hline \end{array}$						25°C	3.2	3.9		
$V_{OL} \text{Low-level output voltage} \qquad V_{ID} = -100 \text{mV}, I_{OL} = 0 \qquad \frac{25^{\circ}\text{C}}{-40^{\circ}\text{C}} \qquad 0 \qquad 50 \\ \hline 85^{\circ}\text{C} \qquad 0 \qquad 50 \\ \hline \\ 4V_{D} \text{Large-signal differential voltage} \\ \text{amplification} \qquad V_{O} = 0.25 \text{V to 2 V}, R_{L} = 100 \text{k}\Omega \qquad \frac{25^{\circ}\text{C}}{-40^{\circ}\text{C}} \qquad 15 \qquad 270 \\ \hline 85^{\circ}\text{C} \qquad 15 \qquad 130 \\ \hline 25^{\circ}\text{C} \qquad 65 \qquad 91 \\ \hline 25^{\circ}\text{C} \qquad 65 \qquad 91 \\ \hline -40^{\circ}\text{C} \qquad 60 \qquad 90 \\ \hline 85^{\circ}\text{C} \qquad 60 \qquad 91 \\ \hline 85^{\circ}\text{C} \qquad 60 \qquad 94 \\ \hline \\ \text{VDD} = 5 \text{V to 10 V}, V_{O} = 1.4 \text{V} \qquad \frac{25^{\circ}\text{C}}{-40^{\circ}\text{C}} \qquad 60 91 \\ \hline 85^{\circ}\text{C} \qquad 60 \qquad 94 \\ \hline \\ \text{VO} = 2.5 \text{V}, \qquad V_{IC} = 2.$	VOH	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 100 \text{ k}\Omega$	-40°C	3	3.9		V
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$						85°C	3	4		
						25°C		0	50	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	-40°C		0	50	mV
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$						85°C		0	50	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$						25°C	25	170		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	AVD		oltage	$V_0 = 0.25 \text{ V to 2 V},$	$R_L = 100 \text{ k}\Omega$	-40°C	15	270		V/mV
CMRR Common-mode rejection ratio $V_{IC} = V_{ICRmin} \qquad \begin{array}{c} -40^{\circ}C & 60 & 90 \\ \hline 85^{\circ}C & 60 & 90 \\ \hline \\ k_{SVR} \qquad \begin{array}{c} \text{Supply-voltage rejection ratio} \\ (\Delta V_{DD}/\Delta V_{IO}) \end{array} \qquad \begin{array}{c} V_{DD} = 5 \text{ V to } 10 \text{ V}, V_{O} = 1.4 \text{ V} \\ \hline \\ 85^{\circ}C \qquad 60 \qquad 91 \\ \hline \\ 85^{\circ}C \qquad 60 \qquad 94 \\ \hline \\ V_{O} = 2.5 \text{ V}, \qquad V_{IC} = 2.5 \text{ V}, \end{array} \qquad \begin{array}{c} 25^{\circ}C \qquad 210 560 \\ \hline \\ 40^{\circ}C \qquad 215 800 \\ \hline \\ \\ 40^{\circ}C \qquad 215 800 \\ \hline \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\$		ampiliication				85°C	15	130		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$						25°C	65	91		
$k_{SVR} = \begin{cases} Supply-voltage \ rejection \ ratio \\ (\Delta V_{DD}/\Delta V_{IO}) \end{cases} V_{DD} = 5 \ V \ to \ 10 \ V, V_{O} = 1.4 \ V \\ \hline V_{DD} = 5 \ V \ to \ 10 \ V, V_{O} = 1.4 \ V \\ \hline 85^{\circ}C = 60 \qquad 94 \end{cases} dE$	CMRR	Common-mode rejection i	atio	V _{IC} = V _{ICR} min		-40°C	60	90		dB
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$						85°C	60	90		
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$						25°C	70	93		
85°C 60 94 V _O = 2.5 V, V _{IC} = 2.5 V, 40°C 315 800 μΑ	k _{SVR}		atio	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	-40°C	60	91		dB
$V_O = 2.5 \text{ V}, \qquad V_{IC} = 2.5 \text{ V}, \qquad 40^{\circ}\text{C}$		(σ. Δ.				85°C	60	94		
						25°C		210	560	
140 1000	I _{DD}	Supply current (two ampli	fiers)		$V_{IC} = 2.5 V,$	-40°C		315	800	μΑ
85°C 160 400				Tito load		85°C		160	400	

[†]Full range is -40°C to 85°C.



^{5.} This range also applies to each input individually.

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electrical characteristics at specified free-air temperature, V_{DD} = 10 V (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	Τ _Α †	TI TI	C27M2 C27M2 C27M2 C27M2	AI BI I	UNIT
						MIN	TYP	MAX	
		TLC27M2I	$V_0 = 1.4 \text{ V},$	$V_{IC} = 0,$	25°C		1.1	10	
			$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			13	mV
		TLC27M2AI	V _O = 1.4 V,	$V_{IC} = 0$,	25°C		0.9	5	
VIO	Input offset voltage		$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			7	
.0		TLC27M2BI	V _O = 1.4 V,	$V_{IC} = 0$,	25°C		224	2000	
			$R_S = 50 \Omega$	$R_L = 100 \text{ k}\Omega$	Full range			3500	μV
		TLC27M7I	$V_0 = 1.4 \text{ V},$	$V_{IC} = 0$,	25°C		190	800	
			$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			2900	
αVIO	Average temperature coeffice offset voltage	cient of input			25°C to 85°C		2.1		μV/°C
lio.	Input offset current (see No	te 4)	V _O = 5 V,	V _{IC} = 5 V	25°C		0.1		рA
lio	input onset current (see No	10 4)	VO = 5 V,	VIC = 3 V	85°C		26	1000	PΛ
					25°C		0.7		
I _{IB}	Input bias current (see Note	e 4)	$V_0 = 5 V$,	$V_{IC} = 5 V$	85°C		220	200 0	pA
V	Common-mode input voltag	je range			25°C	-0.2 to 9	-0.3 to 9.2		V
VICR	(see Note 5)	· ·			Full range	-0.2 to 8.5			V
					25°C	8	8.7		
Vон	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 100 \text{ k}\Omega$	-40°C	7.8	8.7		V
					85°C	7.8	8.7		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	-40°C		0	50	mV
					85°C		0	50	
					25°C	25	275		
A_{VD}	Large-signal differential volt amplification	age	$V_0 = 1 \text{ V to 6 V},$	$R_L = 100 \text{ k}\Omega$	−40°C	15	390		V/mV
	amplification				85°C	15	220		
					25°C	65	94		
CMRR	Common-mode rejection ra	tio	V _{IC} = V _{ICR} min		-40°C	60	93		dB
					85°C	60	94		
					25°C	70	93		
k _{SVR}	Supply-voltage rejection rat (ΔV _{DD} /ΔV _{IO})	10	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	-40°C	60	91		dB
	(= * DD				85°C	60	94		
					25°C		285	600	
I_{DD}	Supply current		V _O = 5 V, No load	$V_{IC} = 5 V$	-40°C		450	900	μΑ
					85°C		205	520	

[†]Full range is -40°C to 85°C.

^{5.} This range also applies to each input individually.



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electrical characteristics at specified free-air temperature, V_{DD} = 5 V (unless otherwise noted)

$V_{IO} = V_{IO} = V$		PARAMETER		TEST CONI	DITIONS	T _A †		.C27M2I .C27M7I		UNIT
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$						``	MIN	TYP	MAX	
$ V_{IOD} \text{Input offset voltage} \begin{array}{c ccccccccccccccccccccccccccccccccccc$			TI COZNIONI	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	
TLC27M7M V _O = 1.4 V, R _S = 50 Ω, R _L = 100 kΩ Full range 3750 αVIO Average temperature coefficient of input offset voltage 1.7 I _{IO} Input offset current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V 25°C 0.1 I _{IB} Input bias current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V V _{IC} = 2.5 V 125°C 0.6 I _{IB} Input bias current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V V _{IC} = 2.5 V 125°C 0.6 I _{IB} Input bias current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V V _{IC} = 2.5 V 125°C 0.6 I _{IB} Input bias current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V V _{IC} = 2.5 V 125°C 0.6 I _{IB} Input bias current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V V _{IC} = 2.5 V 125°C 0.6 I _{IB} Input bias current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V V _{IC} = 2.5 V 125°C 0.6 I _{IB} Input bias current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V V _{IC} = 2.5 V 125°C 0.6 I _{IB} Input bias current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V V _{IC} = 2.5 V V _{IC} = 2.5 V 0.6 I _I Input bias current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V		lanut effect valte es	I LC2/M2M	$R_S = 50 \Omega$		Full range			12	\/
Note Common-mode input voltage Note	۷IO	input offset voltage	TI 00784784	V _O = 1.4 V,	V _{IC} = 0,	25°C		185	500	mV
No Input offset current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V 25°C 0.1 No Input offset current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V 25°C 0.6 No Input bias current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V 25°C 0.6 No Input bias current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V 125°C 9 355 No Input bias current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V 125°C 9 355 No Input bias current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V 125°C 9 355 No Input bias current (see Note 4) V _O = 1.00 mV,			TLC2/M/M			Full range			3750	
Input offset current (see Note 4)	αVIO		cient of input					1.7		μV/°C
In Input bias current (see Note 4) V _O = 2.5 V, V _{IC} = 2.5 V 25°C 0.6 1.4 15 125°C 0.6 12		Land offer terminal for a Nic	(- 4)	V 05V		25°C		0.1		pА
Input bias current (see Note 4) VO = 2.5 V, VIC = 2.5 V VIC = 2.5 V	'IO	input offset current (see No	ite 4)	VO = 2.5 V,	AIC = 5.2 A	125°C		1.4	15	nA
Vicro Common-mode input voltage range (see Note 5) Vide			4)	V 0.5.V		25°C		0.6		pА
$V_{ICR} \begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	IB	input bias current (see Note	9 4)	VO = 2.5 V,	VIC = 5.5 V	125°C		9	35	nA
$V_{OH} \text{High-level output voltage} V_{ID} = 100 \text{mV}, R_L = 100 \text{k}\Omega \qquad 25^{\circ}\text{C} \qquad 3.2 3.9 \\ \hline V_{OL} \text{Low-level output voltage} \qquad V_{ID} = -100 \text{mV}, I_{OL} = 0 \qquad 25^{\circ}\text{C} \qquad 3 3.9 \\ \hline V_{OL} \text{Low-level output voltage} \qquad V_{ID} = -100 \text{mV}, I_{OL} = 0 \qquad 25^{\circ}\text{C} \qquad 0 50 \\ \hline 125^{\circ}\text{C} \qquad 15 290 \\ \hline 125^{\circ}\text{C} \qquad 15 120 \\ \hline 125^{\circ}\text{C} \qquad 15 120 \\ \hline 125^{\circ}\text{C} \qquad 66 91 \\ \hline 125^{\circ}\text{C} \qquad 60 94 $	\/	Common-mode input voltag	ge range			25°C	to	to		V
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	VICR	(see Note 5)	-			Full range	to			V
$V_{OL} \text{Low-level output voltage} \qquad V_{ID} = -100 \text{mV}, I_{OL} = 0 \qquad \begin{array}{c} 125^{\circ}\text{C} & 3 & 4 \\ 25^{\circ}\text{C} & 0 & 50 \\ \hline -55^{\circ}\text{C} & 0 & 50 \\ \hline 125^{\circ}\text{C} & 0 & 50 \\ \hline 125^{\circ}\text{C} & 0 & 50 \\ \hline 125^{\circ}\text{C} & 0 & 50 \\ \hline \end{array}$ $A_{VD} \begin{array}{c} \text{Large-signal differential voltage} \\ \text{amplification} & V_{O} = 0.25 \text{V to 2 V}, R_{L} = 100 \text{k}\Omega \\ \hline \\ V_{O} = 0.25 \text{V to 2 V}, R_{L} = 100 \text{k}\Omega \\ \hline \\ 125^{\circ}\text{C} & 15 & 290 \\ \hline \\ 125^{\circ}\text{C} & 65 & 91 \\ \hline \\ 125^{\circ}\text{C} & 60 & 94 \\ \hline \\ \\ 125^{\circ}\text{C} & 60 & 94 \\ \hline \\ \\ 125^{\circ}\text{C} & 60 & 94 \\ \hline \\ \\ \\ 125^{\circ}\text{C} & 60 & 94 \\ \hline \\ \\ \\ \\ 125^{\circ}\text{C} & 60 & 94 \\ \hline \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ $						25°C	3.2	3.9		
$V_{OL} \text{Low-level output voltage} \qquad V_{ID} = -100 \text{mV}, I_{OL} = 0 \qquad \frac{25^{\circ}\text{C}}{-55^{\circ}\text{C}} \qquad 0 50 \\ \hline 125^{\circ}\text{C} \qquad 15 290 \\ \hline 125^{\circ}\text{C} \qquad 15 120 \\ \hline 125^{\circ}\text{C} \qquad 15 120 \\ \hline 125^{\circ}\text{C} \qquad 60 91 \\ \hline 125^{\circ}\text{C} \qquad 60 94 \\ \hline 125^{\circ}$	Vон	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 100 \text{ k}\Omega$	−55°C	3	3.9		V
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$						125°C	3	4		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$						25°C		0	50	
$ \begin{array}{c} \text{AVD} \underset{\text{amplification}}{\text{Large-signal differential voltage}} \\ \text{AVD} \underset{\text{amplification}}{\text{Large-signal differential voltage}} \\ \text{AVD} \underset{\text{amplification}}{\text{Large-signal differential voltage}} \\ \text{AVD} \underset{\text{boson of the particles}}{\text{Volsion of the particles}} \\ \text{Common-mode rejection ratio} \\ \text{CMRR} \underset{\text{common-mode rejection ratio}}{\text{Common-mode rejection ratio}} \\ \text{Volc} = \text{VolcRmin} \\ \text{Volc} = \text{VolcRmin} \\ \text{Volc} = \text{VolcRmin} \\ \text{Volc} = \text{VolcRmin} \\ \text{Volc} = \text{VolcMode} \\ VolcMod$	V_{OL}	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	−55°C		0	50	mV
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$						125°C		0	50	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$						25°C	25	170		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	A_{VD}	0 0	tage	$V_0 = 0.25 \text{ V to 2 V},$	$R_L = 100 \text{ k}\Omega$	−55°C	15	290		V/mV
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		amplification				125°C	15	120		
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$						25°C	65	91		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	CMRR	Common-mode rejection ra	tio	V _{IC} = V _{ICR} min		−55°C	60	89		dB
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$						125°C	60	91		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$						25°C	70	93		
125°C 60 94 125°C 60 94 125°C 210 560 10	ksvr		io	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	−55°C	60	91		dB
$V_O = 2.5 \text{ V},$ $V_{IC} = 2.5 \text{ V},$ $V_{IC} = 2.5 \text{ V},$ No load $V_O = 2.5 \text{ V},$ No load		(7 A DD / 7 A IO)				125°C	60	94		
IDD Supply current (two amplifiers) No load —55°C 340 880				V 0.5.V		25°C		210	560	
	I_{DD}	Supply current (two amplifie	ers)	"	$V_{IC} = 2.5 \text{ V},$	−55°C		340	880	μΑ
125°C 140 360				1.15 1000		125°C		140	360	

[†] Full range is –55°C to 125°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.

5. This range also applies to each input individually.



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electrical characteristics at specified free-air temperature, V_{DD} = 10 V (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	T _A †		.C27M2N .C27M7N		UNIT
					"	MIN	TYP	MAX	
		TLC27M2M	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	
\	lanut effect valtage	I LC2/M2M	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			12	\/
VIO	Input offset voltage	TLC27M7M	V _O = 1.4 V,	V _{IC} = 0,	25°C		190	800	mV
		I LC2/W//W	$R_S = 50 \Omega$,	$R_L = 100 \text{ k}\Omega$	Full range			4300	
ανιο	Average temperature coeffice offset voltage	ient of input			25°C to 125°C		2.1		μV/°C
1	Innut offeet ourrent (acc Not	o 4\	V- 5.V	\/.a	25°C		0.1		- A
10	Input offset current (see Not	e 4)	V _O = 5 V,	$V_{IC} = 5 V$	125°C		1.8	15	pΑ
1	Innut high current (and Note	4)	V- 5.V	\/.a	25°C		0.7		- A
İΙΒ	Input bias current (see Note	4)	V _O = 5 V,	$V_{IC} = 5 V$	125°C		10	35	pΑ
V: 0.5	Common-mode input voltage	e range			25°C	0 to 9	-0.3 to 9.2		V
VICR	(see Note 5)				Full range	0 to 8.5			V
					25°C	8	8.7		
VOH	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 100 \text{ k}\Omega$	−55°C	7.8	8.6		V
					125°C	7.8	8.8		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$IO\Gamma = 0$	−55°C		0	50	mV
					125°C		0	50	
	Lawrence and all the second all controls				25°C	25	275		
AVD	Large-signal differential volta amplification	age	$V_0 = 1 \text{ V to 6 V},$	$R_L = 100 \text{ k}\Omega$	−55°C	15	420		V/mV
	аттриноалогі				125°C	15	190		
					25°C	65	94		
CMRR	Common-mode rejection rat	io	$V_{IC} = V_{ICR}min$		−55°C	60	93		dB
					125°C	60	93		
	0 1 1/2 1 1/2 1/2				25°C	70	93		
ksvr	Supply-voltage rejection ration (ΔVDD/ΔVIO)	D	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	−55°C	60	91		dB
	(A*DD/A*IO)				125°C	60	94		
			V = F V	\/:- F\/	25°C		285	600	
I_{DD}	Supply current (two amplifie	rs)	V _O = 5 V, No load	$V_{IC} = 5 V$,	−55°C		490	1000	μΑ
					125°C		180	480	

[†] Full range is –55°C to 125°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.

5. This range also applies to each input individually.



operating characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$

	PARAMETER	TEST C	ONDITIONS	TA	TLC27 TLC27 TLC27 TLC27	M2AC M2BC	UNIT
					MIN T	P MA	(
				25°C	0.	43	_
			V _{I(PP)} = 1 V	0°C	0.	46	
SR	Slew rate at unity gain	$R_L = 100 \text{ k}\Omega$		70°C	0.	36	V/μs
JSK	Siew rate at unity gain	C _L = 20 pF, See Figure 1		25°C	0.	40	ν/μδ
			$V_{I(PP)} = 2.5 V$	0°C	0.	43	
				70°C	0.	34	
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$,	25°C		32	nV/√ Hz
				25°C		55	
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$, $R_L = 100 \text{ k}\Omega$,	C _L = 20 pF, See Figure 1	0°C		60	kHz
			occ rigure r	70°C		50	7
		.,		25°C	5	25	
B ₁	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	$C_L = 20 \text{ pF},$	0°C	6	00	kHz
		Occ rigare 3		70°C	4	00	7
)/ 40 ···)/	, 5	25°C	4	0°	
φm	Phase margin	$V_{l} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	f = B ₁ , See Figure 3	0°C	4	1°	
			233100	70°C	3	9°	

operating characteristics at specified free-air temperature, V_{DD} = 10 V

	PARAMETER	TEST C	ONDITIONS	TA	TLC TLC	27M2C 27M2A 27M2B 27M7C	C C	UNIT
					MIN	TYP	MAX	
				25°C		0.62		
			V _{I(PP)} = 1 V	0°C		0.67		
SR	Slow rate of unity gain	$R_L = 100 \text{ k}\Omega$		70°C		0.51		\//uo
J SK	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.56		V/μs
			$V_{I(PP)} = 5.5 V$	0°C		0.61		
			` ′	70°C		0.46		
٧n	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$,	25°C		32		nV/√ Hz
				25°C		35		
BOM	Maximum output-swing bandwidth	$V_O = V_{OH}$, $R_L = 100 \text{ k}\Omega$,		0°C		40		kHz
		K_ = 100 Ks2,	See Figure 1	70°C		30		
				25°C		635		
В1	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	$C_L = 20 pF$,	0°C		710		kHz
		See Figure 3		70°C		510		
				25°C		43°		
φm	Phase margin	$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	f = B ₁ , See Figure 3	0°C		44°		
		OL = 20 pr ,	CCC Figure 5	70°C		42°		

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operating characteristics at specified free-air temperature, $V_{DD} = 5 V$

PARAMETER		TEST CO	ONDITIONS	TA	TLC27M2I TLC27M2AI TLC27M2BI TLC27M7I			UNIT
				MIN	TYP	MAX		
				25°C		0.43		
			V _{I(PP)} = 1 V	−40°C		0.51		
SR	Slew rate at unity gain	$R_L = 100 \text{ k}\Omega$		85°C		0.35		V/μs
	Siew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.40		ν/μ5
			V _{I(PP)} = 2.5 V	−40°C		0.48		
				85°C		0.32		
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$,	25°C		32		nV/√ Hz
			C _L = 20 pF, See Figure 1	25°C		55		
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$, $R_I = 100 \text{ k}\Omega$,		−40°C		75		kHz
			occ riguic r	85°C		45		
				25°C		525		
B ₁	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	$C_L = 20 pF$,	−40°C		770		MHz
		occ rigare s		85°C		370		
)/ 40 ···)/	, D	25°C		40°		
φm	Phase margin	V _I = 10 mV, C _L = 20 pF,	f = B ₁ , See Figure 3	−40°C		43°		
		0L - 20 pi,	2331 194100	85°C		38°		

operating characteristics at specified free-air temperature, $V_{DD} = 10 \text{ V}$

	PARAMETER		ONDITIONS	TA	TLC27M2I TLC27M2AI TLC27M2BI TLC27M7I			UNIT
					MIN	TYP	MAX	
				25°C		0.62		l l
			$V_{I(PP)} = 1 V$	−40°C		0.77		
SR	Slew rate at unity gain	$R_L = 100 \text{ k}\Omega$		85°C		0.47		\////
J SK	Siew rate at utility gain	C _L = 20 pF, See Figure 1		25°C		0.56		V/μs
		Jess rigare r	$V_{I(PP)} = 5.5 V$	−40°C		0.70		1
				85°C		0.44		1
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$,	25°C		32		nV/√ Hz
				25°C		35		
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$, $R_I = 100 \text{ k}\Omega$,	C _L = 20 pF, See Figure 1	−40°C		45		kHz
			Gee rigure r	85°C		25		1
				25°C		635		
В1	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	$C_L = 20 pF$,	−40°C		880		MHz
		occ rigure 3		85°C		480		1
		V 40 V	. 5	25°C		43°		
φm	Phase margin	V _I = 10 mV, C _L = 20 pF,	f = B ₁ , See Figure 3	−40°C		46°]
				85°C		41°		

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operating characteristics at specified free-air temperature, $V_{DD} = 5 V$

	PARAMETER		ONDITIONS	TA	TLC27M2M TLC27M7M			UNIT
					MIN	TYP	MAX	
				25°C		0.43		
			V _{I(PP)} = 1 V	−55°C		0.54		
SR	Class rate at units agin	$R_L = 100 \text{ k}\Omega$		125°C		0.29		\//··a
J SK	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.40		V/μs
			V _{I(PP)} = 2.5 V	−55°C		0.49		
				125°C		0.28		
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$,	25°C		32		nV/√ Hz
		$V_O = V_{OH}$, $R_L = 100 \text{ k}\Omega$,		25°C		55		
ВОМ	Maximum output-swing bandwidth			−55°C		80		kHz
				125°C		40		
				25°C		525		
В1	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	$C_L = 20 \text{ pF},$	−55°C		850		kHz
				125°C		330		1
		\/: 40 m\/	4 D	25°C		40°		
φm	Phase margin	$V_{\parallel} = 10 \text{ mV},$	f = B ₁ , See Figure 3	−55°C		44°		
		ο ρι ,	255garo 0	125°C		36°		

operating characteristics at specified free-air temperature, V_{DD} = 10 V

	PARAMETER	TEST CO	ONDITIONS	TA	TLC27M2M TLC27M7M			UNIT
					MIN	TYP	MAX	1
				25°C		0.62		
			V _{I(PP)} = 1 V	−55°C		0.81]
SR	Claus rate at units ania	$R_L = 100 \text{ k}\Omega$		125°C		0.38		\//··a
SK	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.56		V/μs
			V _{I(PP)} = 5.5 V	−55°C		0.73		1
				125°C		0.35		
V _n	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$,	25°C		32		nV/√ Hz
				25°C		35		
ВОМ	Maximum output-swing bandwidth	V _O = V _{OH} ,	C _L = 20 pF, See Figure 1	−55°C		50		kHz
				125°C		20		1
				25°C		635		
В1	Unity gain bandwidth	V _I = 10 mV, See Figure 3	$C_L = 20 \text{ pF},$	−55°C		960		kHz
	See F			125°C		440		1
)/ 40 ···)/	, 5	25°C		43°		
φm	Phase margin	$V_{l} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	f = B ₁ , See Figure 3	−55°C		47°]
		0L = 20 pr,	Soo i iguic s	125°C		39°		1

PARAMETER MEASUREMENT INFORMATION

single-supply versus split-supply test circuits

Because the TLC27M2 and TLC27M7 are optimized for single-supply operation, circuit configurations used for the various tests often present some inconvenience since the input signal, in many cases, must be offset from ground. This inconvenience can be avoided by testing the device with split supplies and the output load tied to the negative rail. A comparison of single-supply versus split-supply test circuits is shown below. The use of either circuit gives the same result.

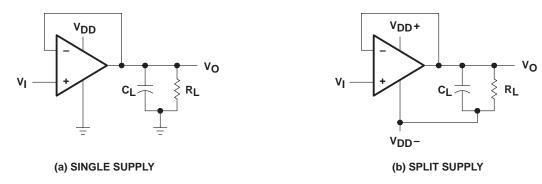


Figure 1. Unity-Gain Amplifier

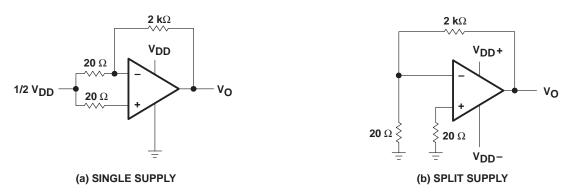


Figure 2. Noise-Test Circuit

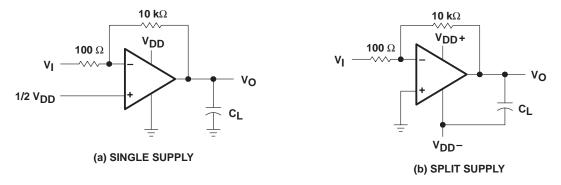


Figure 3. Gain-of-100 Inverting Amplifier

PARAMETER MEASUREMENT INFORMATION

input bias current

Because of the high input impedance of the TLC27M2 and TLC27M7 operational amplifiers, attempts to measure the input bias current can result in erroneous readings. The bias current at normal room ambient temperature is typically less than 1 pA, a value that is easily exceeded by leakages on the test socket. Two suggestions are offered to avoid erroneous measurements:

- 1. Isolate the device from other potential leakage sources. Use a grounded shield around and between the device inputs (see Figure 4). Leakages that would otherwise flow to the inputs are shunted away.
- Compensate for the leakage of the test socket by actually performing an input bias current test (using a picoammeter) with no device in the test socket. The actual input bias current can then be calculated by subtracting the open-socket leakage readings from the readings obtained with a device in the test socket.

One word of caution—many automatic testers as well as some bench-top operational amplifier testers use the servo-loop technique with a resistor in series with the device input to measure the input bias current (the voltage drop across the series resistor is measured and the bias current is calculated). This method requires that a device be inserted into the test socket to obtain a correct reading; therefore, an open-socket reading is not feasible using this method.

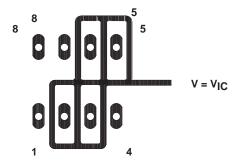


Figure 4. Isolation Metal Around Device Inputs (JG and P packages)

low-level output voltage

To obtain low-supply-voltage operation, some compromise was necessary in the input stage. This compromise results in the device low-level output being dependent on both the common-mode input voltage level as well as the differential input voltage level. When attempting to correlate low-level output readings with those quoted in the electrical specifications, these two conditions should be observed. If conditions other than these are to be used, please refer to Figures 14 through 19 in the Typical Characteristics of this data sheet.

PARAMETER MEASUREMENT INFORMATION

input offset voltage temperature coefficient

Erroneous readings often result from attempts to measure temperature coefficient of input offset voltage. This parameter is actually a calculation using input offset voltage measurements obtained at two different temperatures. When one (or both) of the temperatures is below freezing, moisture can collect on both the device and the test socket. This moisture results in leakage and contact resistance, which can cause erroneous input offset voltage readings. The isolation techniques previously mentioned have no effect on the leakage, since the moisture also covers the isolation metal itself, thereby rendering it useless. It is suggested that these measurements be performed at temperatures above freezing to minimize error.

full-power response

Full-power response, the frequency above which the operational amplifier slew rate limits the output voltage swing, is often specified two ways: full-linear response and full-peak response. The full-linear response is generally measured by monitoring the distortion level of the output while increasing the frequency of a sinusoidal input signal until the maximum frequency is found above which the output contains significant distortion. The full-peak response is defined as the maximum output frequency, without regard to distortion, above which full peak-to-peak output swing cannot be maintained.

Because there is no industry-wide accepted value for significant distortion, the full-peak response is specified in this data sheet and is measured using the circuit of Figure 1. The initial setup involves the use of a sinusoidal input to determine the maximum peak-to-peak output of the device (the amplitude of the sinusoidal wave is increased until clipping occurs). The sinusoidal wave is then replaced with a square wave of the same amplitude. The frequency is then increased until the maximum peak-to-peak output can no longer be maintained (Figure 5). A square wave is used to allow a more accurate determination of the point at which the maximum peak-to-peak output is reached.

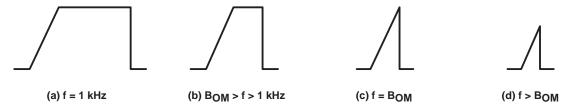


Figure 5. Full-Power-Response Output Signal

test time

Inadequate test time is a frequent problem, especially when testing CMOS devices in a high-volume, short-test-time environment. Internal capacitances are inherently higher in CMOS than in bipolar and BiFET devices and require longer test times than their bipolar and BiFET counterparts. The problem becomes more pronounced with reduced supply levels and lower temperatures.

TYPICAL CHARACTERISTICS

Table of Graphs

			FIGURE
VIO	Input offset voltage	Distribution	6, 7
α VIO	Temperature coefficient	Distribution	8, 9
Vон	High-level output voltage	vs High-level output current vs Supply voltage vs Free-air temperature	10, 11 12 13
V _{OL}	Low-level output voltage	vs Common-mode input voltage vs Differential input voltage vs Free-air temperature vs Low-level output current	14, 15 16 17 18, 19
AVD	Differential voltage amplification	vs Supply voltage vs Free-air temperature vs Frequency	20 21 32, 33
I _{IB} /I _{IO}	Input bias and input offset current	vs Free-air temperature	22
VIC	Common-mode input voltage	vs Supply voltage	23
IDD	Supply current	vs Supply voltage vs Free-air temperature	24 25
SR	Slew rate	vs Supply voltage vs Free-air temperature	26 27
	Normalized slew rate	vs Free-air temperature	28
VO(PP)	Maximum peak-to-peak output voltage	vs Frequency	29
B ₁	Unity-gain bandwidth	vs Free-air temperature vs Supply voltage	30 31
фm	Phase margin	vs Supply voltage vs Free-air temperature vs Capacitive loads	34 35 36
Vn	Equivalent input noise voltage	vs Frequency	37
ф	Phase shift	vs Frequency	32, 33

TYPICAL CHARACTERISTICS

DISTRIBUTION OF TLC27M2 INPUT OFFSET VOLTAGE

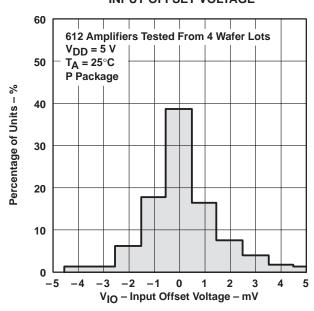


Figure 6

DISTRIBUTION OF TLC27M2 INPUT OFFSET VOLTAGE

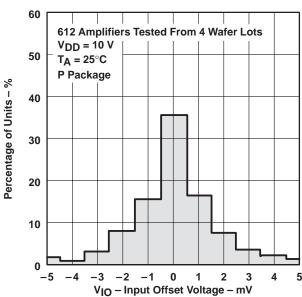


Figure 7

DISTRIBUTION OF TLC27M2 AND TLC27M7 INPUT OFFSET VOLTAGE TEMPERATURE COEFFICIENT

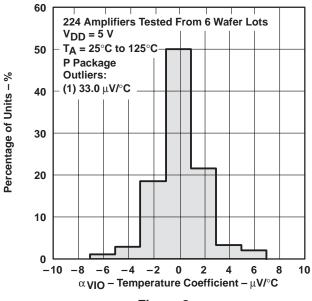


Figure 8

DISTRIBUTION OF TLC27M2 AND TLC27M7 INPUT OFFSET VOLTAGE TEMPERATURE COEFFICIENT

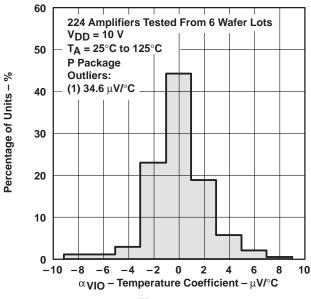
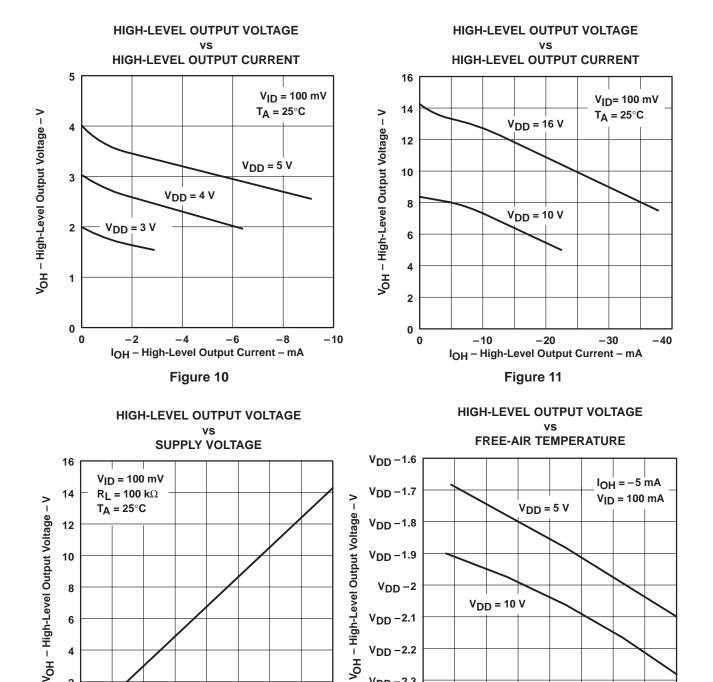


Figure 9



16

4

2

0

0

2

8

V_{DD} – Supply Voltage – V Figure 12

10

12

14



V_{DD} -2.2

V_{DD} -2.3

V_{DD} -2.4

. -75

-50

-25

0

Figure 13

25

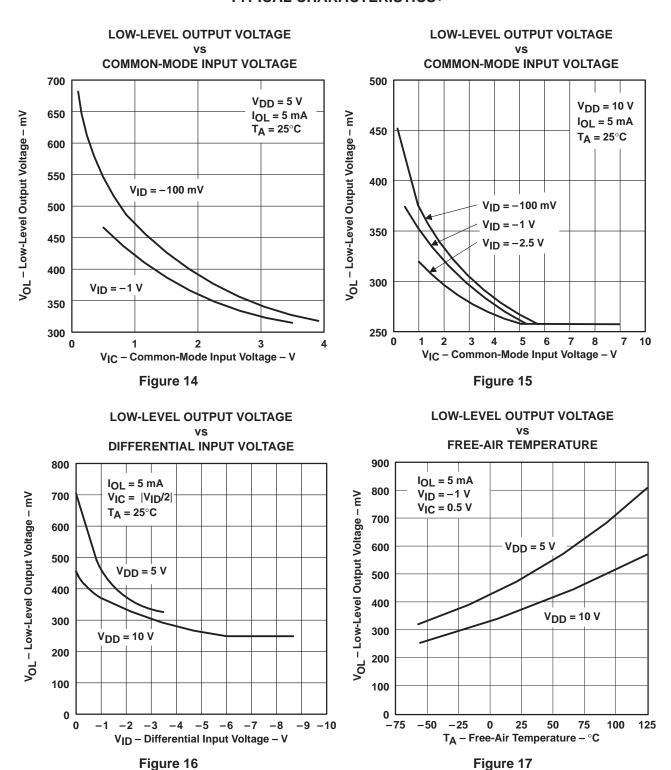
T_A – Free-Air Temperature – °C

50

75

100 125

[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



TYPICAL CHARACTERISTICS†

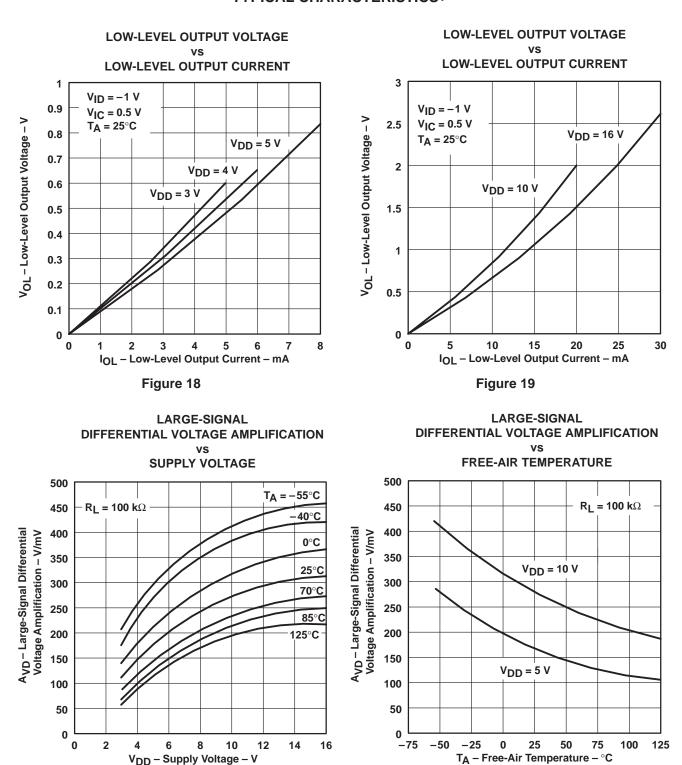


Figure 20

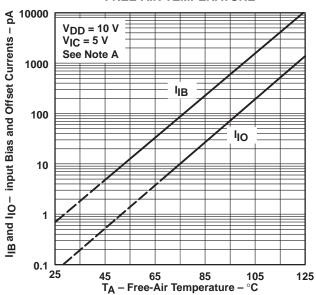


Figure 21

[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

INPUT BIAS CURRENT AND INPUT OFFSET **CURRENT**

vs FREE-AIR TEMPERATURE



NOTE A: The typical values of input bias current and input offset current below 5 pA were determined mathematically.

Figure 22

SUPPLY CURRENT ٧S **SUPPLY VOLTAGE**

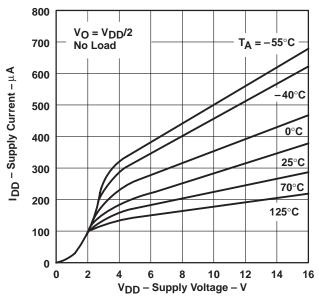


Figure 24

COMMON-MODE INPUT VOLTAGE POSITIVE LIMIT

SUPPLY VOLTAGE

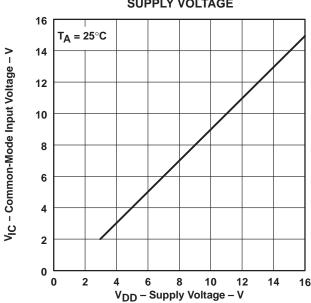


Figure 23

SUPPLY CURRENT

FREE-AIR TEMPERATURE

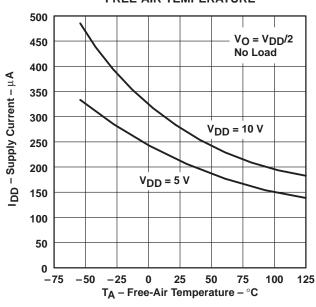
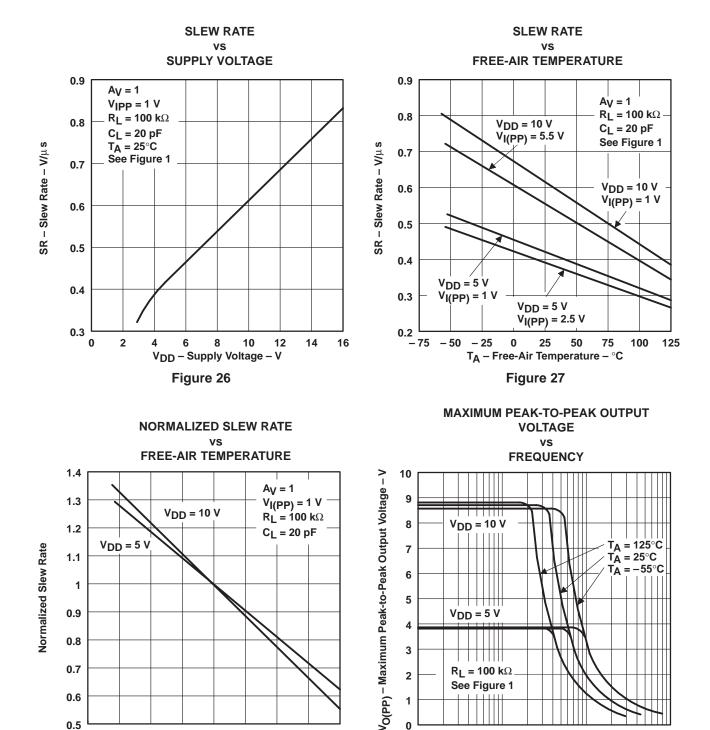


Figure 25

[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.





† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

125

0.7

0.6

0.5

_75

-50

-25

0

25

 T_A – Free-Air Temperature – $^{\circ}C$

Figure 28

50

75

100



 $R_L = 100 \text{ k}\Omega$

See Figure 1

10

f - Frequency - kHz

Figure 29

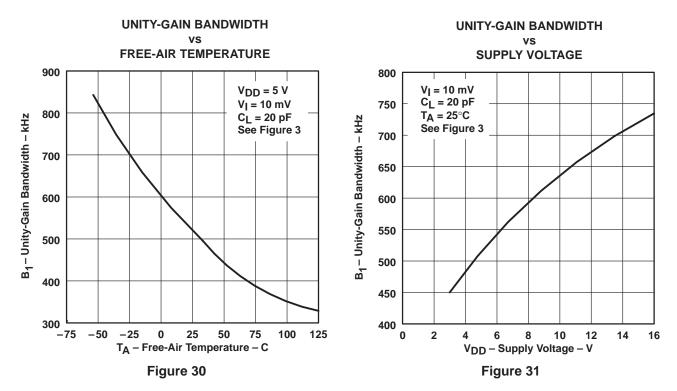
100

2

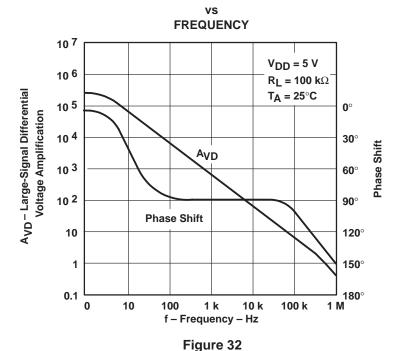
0

1

1000



LARGE-SCALE DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT



[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



LARGE-SCALE DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT

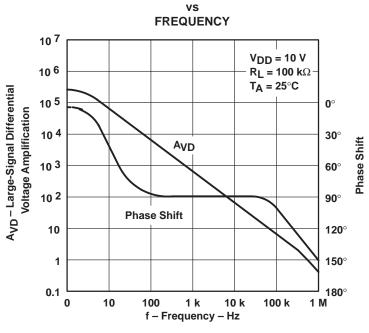
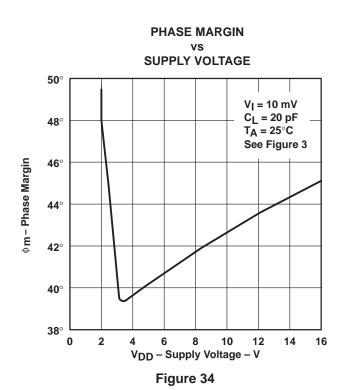
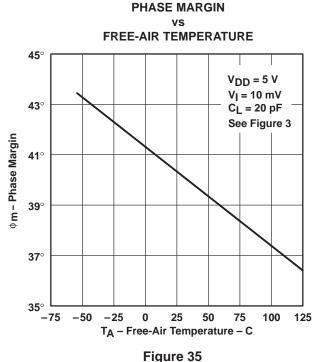


Figure 33





† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



34°

32°

30°

28° 0 10 20

TYPICAL CHARACTERISTICS

PHASE MARGIN vs **CAPACITIVE LOAD 44**° $V_{DD} = 5 V$ **42**° $V_I = 10 \text{ mV}$ T_A = 25°C **40**° See Figure 3 38° 36°

30 40 50 60 70 80 90 100 C_L - Capacitive Load - pF

Figure 36

EQUIVALENT INPUT NOISE VOLTAGE

FREQUENCY

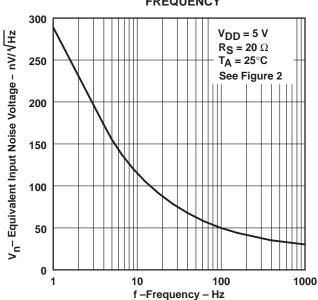


Figure 37

single-supply operation

While the TLC27M2 and TLC27M7 perform well using dual power supplies (also called balanced or split supplies), the design is optimized for single-supply operation. This design includes an input common-mode voltage range that encompasses ground as well as an output voltage range that pulls down to ground. The supply voltage range extends down to 3 V (C-suffix types), thus allowing operation with supply levels commonly available for TTL and HCMOS; however, for maximum dynamic range, 16-V single-supply operation is recommended.

Many single-supply applications require that a voltage be applied to one input to establish a reference level that is above ground. A resistive voltage divider is usually sufficient to establish this reference level (see Figure 38). The low input bias current of the TLC27M2 and TLC27M7 permits the use of very large resistive values to implement the voltage divider, thus minimizing power consumption.

The TLC27M2 and TLC27M7 work well in conjunction with digital logic; however, when powering both linear devices and digital logic from the same power supply, the following precautions are recommended:

- 1. Power the linear devices from separate bypassed supply lines (see Figure 39); otherwise, the linear device supply rails can fluctuate due to voltage drops caused by high switching currents in the digital logic.
- 2. Use proper bypass techniques to reduce the probability of noise-induced errors. Single capacitive decoupling is often adequate; however, high-frequency applications may require RC decoupling.

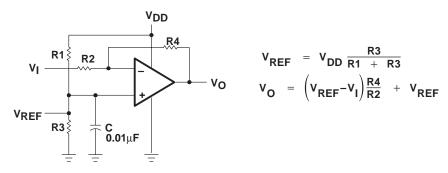
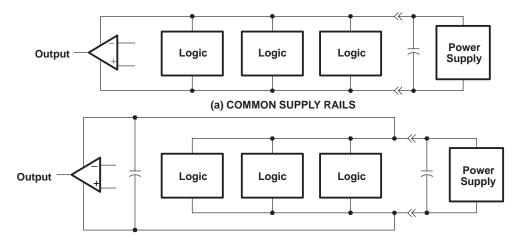


Figure 38. Inverting Amplifier With Voltage Reference



(b) SEPARATE BYPASSED SUPPLY RAILS (preferred)

Figure 39. Common Versus Separate Supply Rails



APPLICATION INFORMATION

input characteristics

The TLC27M2 and TLC27M7 are specified with a minimum and a maximum input voltage that, if exceeded at either input, could cause the device to malfunction. Exceeding this specified range is a common problem, especially in single-supply operation. Note that the lower range limit includes the negative rail, while the upper range limit is specified at V_{DD} –1 V at T_A = 25°C and at V_{DD} –1.5 V at all other temperatures.

The use of the polysilicon-gate process and the careful input circuit design gives the TLC27M2 and TLC27M7 very good input offset voltage drift characteristics relative to conventional metal-gate processes. Offset voltage drift in CMOS devices is highly influenced by threshold voltage shifts caused by polarization of the phosphorus dopant implanted in the oxide. Placing the phosphorus dopant in a conductor (such as a polysilicon gate) alleviates the polarization problem, thus reducing threshold voltage shifts by more than an order of magnitude. The offset voltage drift with time has been calculated to be typically $0.1\mu V/month$, including the first month of operation.

Because of the extremely high input impedance and resulting low bias current requirements, the TLC27M2 and TLC27M7 are well suited for low-level signal processing; however, leakage currents on printed-circuit boards and sockets can easily exceed bias current requirements and cause a degradation in device performance. It is good practice to include guard rings around inputs (similar to those of Figure 4 in the Parameter Measurement Information section). These guards should be driven from a low-impedance source at the same voltage level as the common-mode input (see Figure 40).

The inputs of any unused amplifiers should be tied to ground to avoid possible oscillation.

noise performance

The noise specifications in operational amplifier circuits are greatly dependent on the current in the first-stage differential amplifier. The low input bias current requirements of the TLC27M2 and TLC27M7 result in a very low noise current, which is insignificant in most applications. This feature makes the devices especially favorable over bipolar devices when using values of circuit impedance greater than $50\,\mathrm{k}\Omega$, since bipolar devices exhibit greater noise currents.

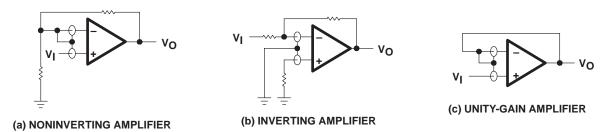


Figure 40. Guard-Ring Schemes

output characteristics

The output stage of the TLC27M2 and TLC27M7 is designed to sink and source relatively high amounts of current (see typical characteristics). If the output is subjected to a short-circuit condition, this high current capability can cause device damage under certain conditions. Output current capability increases with supply voltage.

All operating characteristics of the TLC27M2 and TLC27M7 were measured using a 20-pF load. The devices drive higher capacitive loads; however, as output load capacitance increases, the resulting response pole occurs at lower frequencies, thereby causing ringing, peaking, or even oscillation (see Figure 41). In many cases, adding a small amount of resistance in series with the load capacitance alleviates the problem.



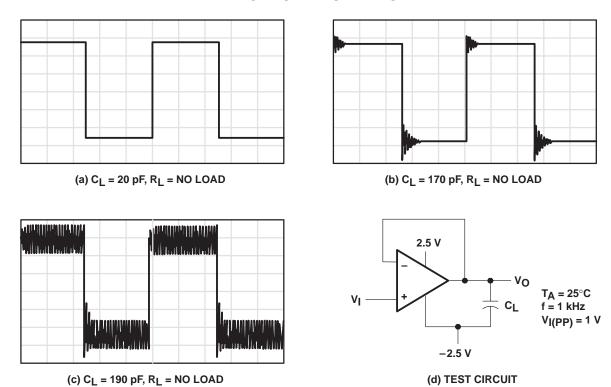
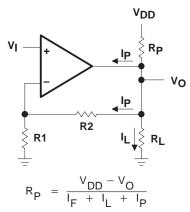


Figure 41. Effect of Capacitive Loads and Test Circuit

output characteristics (continued)

Although the TLC27M2 and TLC27M7 possess excellent high-level output voltage and current capability, methods for boosting this capability are available, if needed. The simplest method involves the use of a pullup resistor (R_P) connected from the output to the positive supply rail (see Figure 42). There are two disadvantages to the use of this circuit. First, the NMOS pulldown transistor N4 (see equivalent schematic) must sink a comparatively large amount of current. In this circuit, N4 behaves like a linear resistor with an on-resistance between approximately $60\,\Omega$ and $180\,\Omega$, depending on how hard the op amp input is driven. With very low values of R_P, a voltage offset from 0 V at the output occurs. Second, pullup resistor R_P acts as a drain load to N4 and the gain of the operational amplifier is reduced at output voltage levels where N5 is not supplying the output current.

output characteristics (continued)



Ip = Pullup current required by the operational amplifier (typically 500 μA)

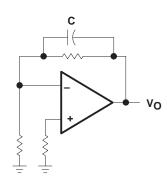


Figure 42. Resistive Pullup to Increase VOH

Figure 43. Compensation for Input Capacitance

feedback

Operational amplifier circuits nearly always employ feedback, and since feedback is the first prerequisite for oscillation, some caution is appropriate. Most oscillation problems result from driving capacitive loads (discussed previously) and ignoring stray input capacitance. A small-value capacitor connected in parallel with the feedback resistor is an effective remedy (see Figure 43). The value of this capacitor is optimized empirically.

electrostatic-discharge protection

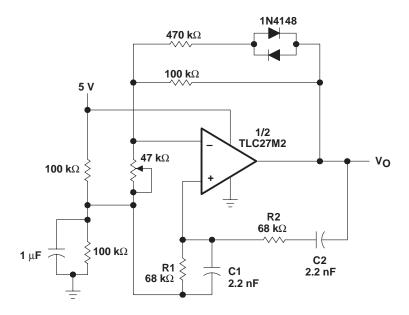
The TLC27M2 and TLC27M7 incorporate an internal electrostatic-discharge (ESD) protection circuit that prevents functional failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015.2. Care should be exercised, however, when handling these devices as exposure to ESD may result in the degradation of the device parametric performance. The protection circuit also causes the input bias currents to be temperature dependent and have the characteristics of a reverse-biased diode.

latch-up

Because CMOS devices are susceptible to latch-up due to their inherent parasitic thyristors, the TLC27M2 and TLC27M7 inputs and outputs were designed to withstand -100-mA surge currents without sustaining latch-up; however, techniques should be used to reduce the chance of latch-up whenever possible. Internal protection diodes should not, by design, be forward biased. Applied input and output voltage should not exceed the supply voltage by more than 300 mV. Care should be exercised when using capacitive coupling on pulse generators. Supply transients should be shunted by the use of decoupling capacitors (0.1 μ F typical) located across the supply rails as close to the device as possible.

The current path established if latch-up occurs is usually between the positive supply rail and ground and can be triggered by surges on the supply lines and/or voltages on either the output or inputs that exceed the supply voltage. Once latch-up occurs, the current flow is limited only by the impedance of the power supply and the forward resistance of the parasitic thyristor and usually results in the destruction of the device. The chance of latch-up occurring increases with increasing temperature and supply voltages.

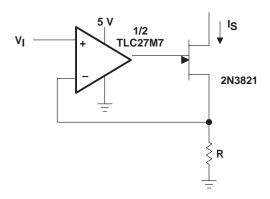




NOTES:
$$V_{O(PP)} \approx 2 \text{ V}$$

$$f_{O} = \frac{1}{2\pi\sqrt{R1R2C1C2}}$$

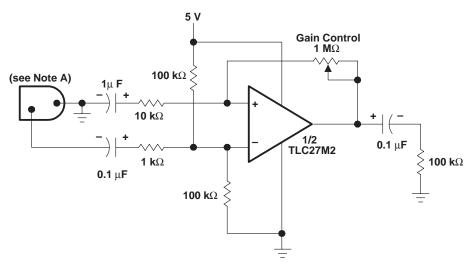
Figure 44. Wien Oscillator



NOTES:
$$V_I = 0 \text{ V to } 3 \text{ V}$$

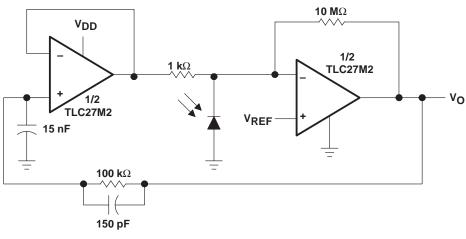
$$I_S = \frac{V_I}{R}$$

Figure 45. Precision Low-Current Sink



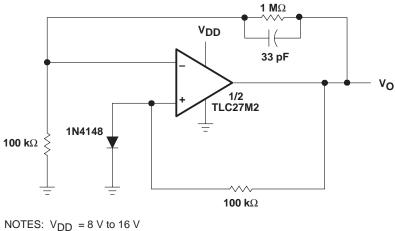
NOTE A: Low to medium impedance dynamic mike

Figure 46. Microphone Preamplifier



NOTES: $V_{DD} = 4 \text{ V to } 15 \text{ V}$ $V_{ref} = 0 \text{ V to } V_{DD} - 2 \text{ V}$

Figure 47. Photo-Diode Amplifier With Ambient Light Rejection



NOTES: $V_{DD} = 8 \text{ V to } 16 \text{ V}$ $V_{O} = 5 \text{ V}, 10 \text{ mA}$

Figure 48. 5-V Low-Power Voltage Regulator

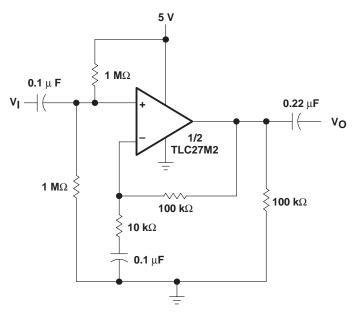


Figure 49. Single-Rail AC Amplifiers



PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TLC27M2ACD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2ACDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2ACDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2ACDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2ACP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2ACPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2AID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2AIDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2AIDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2AIDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2AIP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2AIPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2BCD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2BCDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2BCDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2BCDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2BCP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2BCPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2BID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2BIDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2BIDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2BIDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2BIP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2BIPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2CD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM





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Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TLC27M2CDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2CDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2CDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2CP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2CPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2CPSLE	OBSOLETE	SO	PS	8		TBD	Call TI	Call TI
TLC27M2CPSR	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2CPSRG4	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2CPW	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2CPWG4	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2CPWLE	OBSOLETE	TSSOP	PW	8		TBD	Call TI	Call TI
TLC27M2CPWR	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2CPWRG4	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2ID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2IDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2IDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2IDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2IP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2IPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2IPW	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2IPWG4	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2IPWR	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2IPWRG4	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2MD	ACTIVE	SOIC	D	8	75	TBD	CU NIPDAU	Level-1-220C-UNLIN
TLC27M2MDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2MDR	OBSOLETE	SOIC	D	8		TBD	Call TI	Call TI
TLC27M2MFKB	OBSOLETE	LCCC	FK	20		TBD	Call TI	Call TI
TLC27M2MJG	OBSOLETE	CDIP	JG	8		TBD	Call TI	Call TI





com 11-Oct-2007

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TLC27M2MJGB	OBSOLETE	CDIP	JG	8		TBD	Call TI	Call TI
TLC27M7CD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M7CDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M7CDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M7CDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M7CP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M7CPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M7CPSR	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M7CPSRG4	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M7ID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M7IDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M7IDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M7IDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M7IP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M7IPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M7MFKB	OBSOLETE	LCCC	FK	20		TBD	Call TI	Call TI
TLC27M7MJG	OBSOLETE	CDIP	JG	8		TBD	Call TI	Call TI
TLC27M7MJGB	OBSOLETE	CDIP	JG	8	_	TBD	Call TI	Call TI
TLC27M7MUB	OBSOLETE	CFP	U	10		TBD	Call TI	Call TI

 $^{^{(1)}}$ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)



PACKAGE OPTION ADDENDUM

11-Oct-2007

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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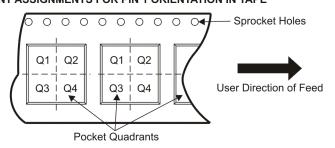
TAPE AND REEL INFORMATION



TAPE DIMENSIONS + K0 - P1 - B0 W Cavity - A0 -

	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLC27M2ACDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC27M2AIDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC27M2BCDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC27M2BIDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC27M2CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC27M2CPSR	SO	PS	8	2000	330.0	16.4	8.2	6.6	2.5	12.0	16.0	Q1
TLC27M2CPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
TLC27M2IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC27M2IPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
TLC27M7CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC27M7CPSR	SO	PS	8	2000	330.0	16.4	8.2	6.6	2.5	12.0	16.0	Q1
TLC27M7IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1





*All dimensions are nominal

All difficultions are norminal							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLC27M2ACDR	SOIC	D	8	2500	340.5	338.1	20.6
TLC27M2AIDR	SOIC	D	8	2500	340.5	338.1	20.6
TLC27M2BCDR	SOIC	D	8	2500	346.0	346.0	29.0
TLC27M2BIDR	SOIC	D	8	2500	346.0	346.0	29.0
TLC27M2CDR	SOIC	D	8	2500	340.5	338.1	20.6
TLC27M2CPSR	SO	PS	8	2000	346.0	346.0	33.0
TLC27M2CPWR	TSSOP	PW	8	2000	346.0	346.0	29.0
TLC27M2IDR	SOIC	D	8	2500	340.5	338.1	20.6
TLC27M2IPWR	TSSOP	PW	8	2000	346.0	346.0	29.0
TLC27M7CDR	SOIC	D	8	2500	346.0	346.0	29.0
TLC27M7CPSR	SO	PS	8	2000	346.0	346.0	33.0
TLC27M7IDR	SOIC	D	8	2500	346.0	346.0	29.0

D (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 (0,15) per end.
- Body width does not include interlead flash. Interlead flash shall not exceed .017 (0,43) per side.
- E. Reference JEDEC MS-012 variation AA.



FK (S-CQCC-N**)

28 TERMINAL SHOWN

LEADLESS CERAMIC CHIP CARRIER



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a metal lid.
- D. The terminals are gold plated.
- E. Falls within JEDEC MS-004



PW (R-PDSO-G**)

14 PINS SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

D. Falls within JEDEC MO-153



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001

For the latest package information, go to http://www.ti.com/sc/docs/package/pkg_info.htm

JG (R-GDIP-T8)

CERAMIC DUAL-IN-LINE

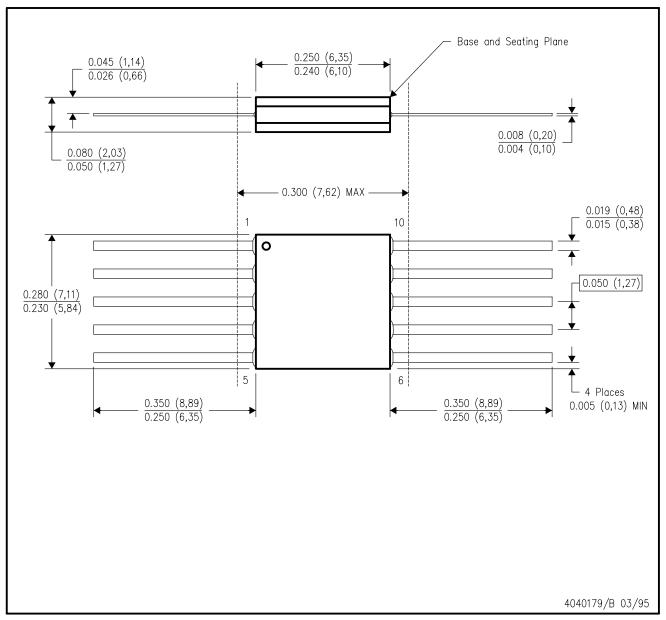


NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification.
- E. Falls within MIL STD 1835 GDIP1-T8

U (S-GDFP-F10)

CERAMIC DUAL FLATPACK



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only.
- E. Falls within MIL STD 1835 GDFP1-F10 and JEDEC MO-092AA



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